Dual Channel Synchronous Gate Driver for Enhancement Mode GaN Transistors

**General Description**

uP1966D has a single PWM input which is designed to effectively drive both the high-side and low-side enhancement mode Gallium Nitride(GaN) FETs in a synchronous buck regulator application. The floating high-side driver is capable of operating up to 40V.

The uP1966D integrates an adjustable dead time controller, capable of independently setting both high to low and low to high dead times. These dead times are set via external resistors.

The uP1966D has two separate high current gate outputs for both high and low side GaN devices. The two outputs allow for independent adjustment of GaN MOSFET turn-on and turn-off speeds by adding an impedance in series with the respective gate. It features fast-switching speed and minimum propagation delay facilitating high-frequency operation. The uP1966D can operate up to several MHz depending on the application. This device also supports bias supply input under voltage lockout. The uP1966D comes in a WLCSP 1.6x1.6-12B package which minimizes package inductance.

**Features**

- 0.4Ω / 0.7 Ω Pull-Down/Pull-Up Resistance
- Independent Dead Time Adjustment
- Adjustable Output for Turn-On/Turn-Off Ability
- Fast Propagation Delays (15ns, Typical)
- Fast Rise and Fall Times (8ns/4ns, Typical)
- CMOS Compatible Input-Logic Threshold (Independent of Supply Voltage)
- Single 5V Driving Voltage Output
- Three PWM Input States: High, Low and Hi Z
- Hi Z Input for DCM operation
- Under Voltage Lockout for Supply Input
- WLCSP 1.6x1.6-12B Package
- RoHS Compliant and Halogen Free
- Low Charge Injection
- Fast Switching Time

**Applications**

- Synchronous Converters

**Ordering Information**

<table>
<thead>
<tr>
<th>Order Number</th>
<th>Package</th>
<th>Top Marking</th>
</tr>
</thead>
<tbody>
<tr>
<td>uP1966DFBB</td>
<td>WLCSP1.6x1.6-12B</td>
<td>TBD</td>
</tr>
</tbody>
</table>

**Notes:**

1. Please check the sample/production availability with uPI representatives.
2. uPI products are compatible with the current IPC/JEDEC J-STD-020 requirement. They are halogen-free, RoHS compliant and 100% matte tin (Sn) plating that are suitable for use in SnPb or Pb-free soldering processes.
**Recommended Operating Conditions**

- Operating Junction Temperature Range: 40°C to +125°C
- Supply Input Voltage, VCC: +4.5V to +5.5V
- Power Input Voltage, VIN: +4.5V to +40V

**Absolute Maximum Ratings**

- Supply Input Voltage, VCC: -0.3V to +7V
- BOOT to PHASE: -0.3V to +7V
- UGH, UGL: (PHASE-0.3V) to (BOOT +0.3V)
- LGH, LGL: -0.3V to (VCC+0.3V)
- PWM: 0V to +40V
- DTH, DTL: 0.3V to +7V
- BOOT to VCC: -0.3V to +7V
- PHASE to GND: 0V to +40V
- BOO to GND: 0V to +45.5V
- Storage Temperature Range: 55°C to +150°C
- Junction Temperature: +150°C
- ESD Rating: ±2kV

**Thermal Information**

- Package Thermal Resistance:
  - WLCSP 1.6x1.6-12BθJA: 76.8°C/W
  - WLCSP 1.6x1.6-12BθAB: 0.6°C/W
  - WLCSP 1.6x1.6-12BθJC: 0.65°C/W

**Notes:**

1. The device is not guaranteed to function outside its recommended operating conditions.
2. Stresses above Absolute Maximum Ratings may cause permanent damage to the device. Functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.
3. Devices are ESD sensitive. Handling precaution recommended.
4. θJA are measured in natural convection at Ta = 25°C on a low thermal conductivity test board using JEDEC 51-3 thermal measurement standard.

**uPI Semiconductor Corp.**

**Headquarters**
9F, No.5, Taiyuan 1st St.
Zhubei City, Hsinchu Taiwan, R.O.C
TEL: 886.3.560.1666 FAX: 886.3.560.1888

**USA**

uPI Semiconductor Inc. Office
T : +1-650-386-1403
2200 Reinert Rd #3 Mountain View CA 94043 USA